# 《风光欣》技术资料

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# A44

## NPN EPITAXIAL SILICON TRANSISTOR

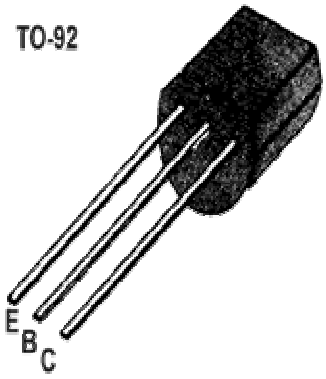
HIGH VOLTA TRNSISTOR

*Collector-Emitter Voltage: $V_{CEO}$=400V

*Collector Dissipation:Pc(max)=625mW

## ABSOLUTE MAXIMUM RATINGS(TA=25 ℃)

| Characteristic | Symbol | Rating | Unit |
|---|---|---|---|
| Collector-Base Voltage | $V_{CBO}$ | 500 | V |
| Collector-Emitter Voltage | $V_{CEO}$ | 500 | V |
| Emitter -Base Voltage | $V_{EBO}$ | 6 | V |
| Collector Current | Ic | 300 | mA |
| Collector Dissipation($T_A$=25℃) | Pc | 625 | mW |
| Collector Dissipation($T_C$=25℃) | Pc | 1.5 | W |
| Junction Temperature | $T_J$ | 150 | ℃ |
| Storage Temperature | $T_{STG}$ | -55 ~150 | ℃ |




## ELECTRCAL CHARACTERISTICS(TA=25 ℃)

| Characteristic | Symbol | Test Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| Collector-Base Breakdown Voltage | $BV_{CBO}$ | Ic=100 μ A,$I_E$=0 | 500 | | V |
| Collector-Emitter Breakdown Voltage | $BV_{CEO}$ | Ic=1mA,$I_B$=0 | 500 | | V |
| Emitter-Base Breakdown Voltage | $BV_{EBO}$ | $I_E$= 100 μ A,Ic=0 | 6 | | V |
| Collector Cut-off Current | $I_{CBO}$ | $V_{CB}$= 400V,$I_E$=0 | | 100 | nA |
| Emitter Cut-off Current | $I_{EBO}$ | $V_{EB}$= 4V, $I_C$=0 | | 100 | nA |
| *DC Current Gain | $H_{FE}$ | $V_{CE}$= 10V,Ic= 1mA | 40 | | |
| | | $V_{CE}$= 10V,Ic= 10mA | 50 | 200 | |
| | | $V_{CE}$= 10V,Ic= 50mA | 45 | | |
| Collector-Emitter Saturation Voltage | $V_{CE}$(sat) | Ic= 1mA,$I_B$=0.1 mA | | 0.4 | V |
| | $V_{CE}$(sat) | Ic= 10mA,$I_B$= 1mA | | 0.5 | V |
| | $V_{CE}$(sat) | Ic= 50mA,$I_B$= 5mA | | 0.75 | V |
| Base-Emitter Saturation Voltage | $V_{BE}$(sat) | Ic= 10mA,$I_B$= 1mA | | 0.75 | V |
| Collector-Base Capacitance | $C_{CB}$ | $V_{CB}$= 20V,$I_E$= 0,F=1MHZ | | 7 | pF |